Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming an amorphous semiconductor film having an upper surface;

forming a first crystalline region by irradiating a laser beam to a first region of **[[an]]** the upper surface of the amorphous semiconductor film by relatively moving the laser beam in a first direction with respect to the first region of **[[said]]** the amorphous semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the upper surface of the amorphous semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in a direction parallel to the first direction with respect to **[[said]]** the second region of the amorphous semiconductor film;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the first direction.

Claim 2 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming an amorphous semiconductor film having an upper surface;

forming a first crystalline region by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular shape to a first region of **[[an]]** the upper surface of the amorphous semiconductor film by relatively moving the laser beam in a first

direction with respect to the first region of **[[said]]** the upper surface of the amorphous semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the upper surface of the amorphous semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in a direction parallel to the first direction with respect to **[[said]]** the second region of the upper surface of the amorphous semiconductor film;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the first direction.

Claim 3 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming an amorphous semiconductor film having an upper surface;

forming a first crystalline region by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or rectangular shape to a first region of **[[an]]** the upper surface of the amorphous semiconductor film by relatively moving the laser beam in a short direction of the laser beam with respect to **[[said]]** the first region of the upper surface of the amorphous semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the upper surface of the amorphous semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in the short direction of the laser beam with respect to **[[said]]** the second region of the upper surface of the amorphous semiconductor film;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the short direction of the laser beam.

Claim 4 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming an amorphous semiconductor film having an upper surface;

a **[[first]]** second step of forming a first crystalline semiconductor film by partially crystallizing **[[an]]** the upper surface of the amorphous semiconductor film by a heating treatment; and

a **[[second]]** third step of forming a second crystalline semiconductor film by irradiating a laser beam to the crystalline semiconductor film;

wherein the **[[second]]** third step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film by relatively moving the laser beam in a first direction with respect to the first region of the first crystalline semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in a direction parallel to the first direction with respect to **[[said]]** the second region of the first crystalline semiconductor film; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the first direction.

Claim 5 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming an amorphous semiconductor film having an upper surface;

a **[[first]]** second step of forming a first crystalline semiconductor film by partially crystallizing **[[an]]** the upper surface of the amorphous semiconductor film by a heating treatment; and

a **[[second]]** third step of forming a second crystalline semiconductor film by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular shape to the first crystalline semiconductor film;

wherein the **[[second]]** third step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film by relatively moving the laser beam in a first direction with respect to the first region of the first crystalline semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in a direction parallel to the first direction with respect to **[[said]]** the second region of the first crystalline semiconductor film; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the first direction.

Claim 6 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming an amorphous semiconductor film having an upper surface;

a **[[first]]** second step of forming a first crystalline semiconductor film by partially crystallizing **[[an]]** the upper surface of the amorphous semiconductor film by a heating treatment; and

a **[[second]]** third step of forming a second crystalline semiconductor film by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular

shape to the first crystalline semiconductor film while relatively moving the laser beam in a short direction of the laser beam with respect to the first crystalline semiconductor film;

wherein the **[[second]]** third step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film by relatively moving the laser beam in the short direction of the laser beam with respect to the first region of the first crystalline semiconductor film; and

after **[[fully]]** forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including a portion of the first crystalline region by relatively moving the laser beam in the short direction of the laser beam with respect to the second region of the first crystalline semiconductor film; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm,

the second crystalline region overlaps with the first crystalline region along the short direction of the laser beam.

Claim 7 (Original): The method of fabricating a semiconductor device according to claim 1, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 8 (Original): The method of fabricating a semiconductor device according to claim 2, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 9 (Original): The method of fabricating a semiconductor device according to claim 3, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim10 (Original): The method of fabricating a semiconductor device according to claim 4, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 11 (Original): The method of fabricating a semiconductor device according to claim 5, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 12 (Original): The method of fabricating a semiconductor device according to claim 6, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 13 (Previously Presented): The method of fabricating a semiconductor device according to claim 1, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 14 (Previously Presented): The method of fabricating a semiconductor device according to claim 2, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 15 (Previously Presented): The method of fabricating a semiconductor device according to claim 3, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 16 (Previously Presented): The method of fabricating a semiconductor device according to claim 4, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 17 (Previously Presented): The method of fabricating a semiconductor device according to claim 5, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 18 (Previously Presented): The method of fabricating a semiconductor device according to claim 6, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim19 (Previously Presented): The method of fabricating a semiconductor device according to claim 1, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 20 (Previously Presented): The method of fabricating a semiconductor device according to claim 2, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 21 (Previously Presented): The method of fabricating a semiconductor device according to claim 3, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 22 (Previously Presented): The method of fabricating a semiconductor device according to claim 4, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 23 (Previously Presented): The method of fabricating a semiconductor device according to claim 5, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 24 (Previously Presented): The method of fabricating a semiconductor device according to claim 6, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 25 (Currently Amended): The method of fabricating a semiconductor device according to claim 1, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 26 (Currently Amended): The method of fabricating a semiconductor device according to claim 2, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 27 (Currently Amended): The method of fabricating a semiconductor device according to claim 3, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 28 (Currently Amended): The method of fabricating a semiconductor device according to claim 4, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 29 (Currently Amended): The method of fabricating a semiconductor device according to claim 5, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 30 (Currently Amended): The method of fabricating a semiconductor device according to claim 6, wherein **[[said]]** the laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.